

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process) (Bias Resistor Built-in Transistor)

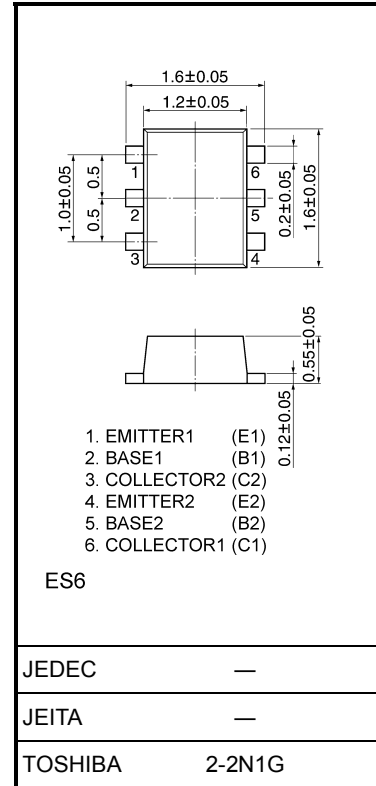
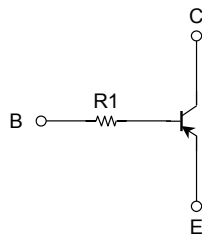
RN2910FE, RN2911FE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

Unit: mm

- Two devices are incorporated into an Extreme-Super-Mini (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
- Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN1910FE, RN1911FE

Equivalent Circuit and Bias Resistor Values



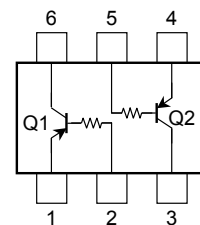
Weight: 0.003g (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C (Note)	100	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Total rating

Equivalent Circuit (top view)



Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = -50\text{ V}, I_E = 0$	—	—	-100	nA
Emitter cut-off current		I_{EBO}	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-100	nA
DC current gain		h_{FE}	$V_{CE} = -5\text{ V}, I_C = -1\text{ mA}$	120	—	400	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	-0.1	-0.3	V
Transition frequency		f_T	$V_{CE} = -10\text{ V}, I_C = -5\text{ mA}$	—	200	—	MHz
Collector output capacitance		C_{ob}	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3	6	pF
Input resistor	RN2910FE	R1	—	3.29	4.7	6.11	kΩ
	RN2911FE			7	10	13	

